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## REVISION HISTORY

### 9/2016—Rev. E to Rev. F

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### 11/2010—Rev. D to Rev. E

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### 9/2006—Rev. 0 to Rev. A

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### 10/2005—Revision 0: Initial Version

## SPECIFICATIONS

## ADR440 ELECTRICAL CHARACTERISTICS

$V_{IN} = 3\text{ V to }18\text{ V}$ ,  $T_A = 25^\circ\text{C}$ ,  $C_{IN} = C_{OUT} = 0.1\ \mu\text{F}$ , unless otherwise noted.

Table 2.

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
OUTPUT VOLTAGE	$V_O$					
A Grade			2.045	2.048	2.051	V
B Grade			2.047	2.048	2.049	V
INITIAL ACCURACY	$V_{OERR}$					
A Grade					3	mV
					0.15	%
B Grade					1	mV
					0.05	%
TEMPERATURE DRIFT	$TCV_O$					
A Grade		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$		2	10	ppm/ $^\circ\text{C}$
B Grade		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$		1	3	ppm/ $^\circ\text{C}$
LINE REGULATION	$\Delta V_O/\Delta V_{IN}$	$-40^\circ\text{C} < T_A < +125^\circ\text{C}$	-20	+10	+20	ppm/V
LOAD REGULATION	$\Delta V_O/\Delta I_{LOAD}$	$I_{LOAD} = 0\text{ mA to }10\text{ mA}$ , $V_{IN} = 3.5\text{ V}$ , $-40^\circ\text{C} < T_A < +125^\circ\text{C}$	-50		+50	ppm/mA
	$\Delta V_O/\Delta I_{LOAD}$	$I_{LOAD} = 0\text{ mA to }-5\text{ mA}$ , $V_{IN} = 3.5\text{ V}$ , $-40^\circ\text{C} < T_A < +125^\circ\text{C}$	-50		+50	ppm/mA
QUIESCENT CURRENT	$I_{IN}$	No load, $-40^\circ\text{C} < T_A < +125^\circ\text{C}$		3	3.75	mA
VOLTAGE NOISE	$e_N$ p-p	0.1 Hz to 10 Hz		1		$\mu\text{V p-p}$
VOLTAGE NOISE DENSITY	$e_N$	1 kHz		45		nV/ $\sqrt{\text{Hz}}$
TURN-ON SETTLING TIME	$t_R$			10		$\mu\text{s}$
LONG-TERM STABILITY <sup>1</sup>	$V_O$	1000 hours		50		ppm
OUTPUT VOLTAGE HYSTERESIS	$V_{O\_HYS}$			70		ppm
RIPPLE REJECTION RATIO	RRR	$f_{IN} = 1\text{ kHz}$		-80		dB
SHORT CIRCUIT TO GND	$I_{SC}$			27		mA
SUPPLY VOLTAGE OPERATING RANGE	$V_{IN}$		3		18	V
SUPPLY VOLTAGE HEADROOM	$V_{IN} - V_O$		500			mV

<sup>1</sup> The long-term stability specification is noncumulative. The drift in the subsequent 1000-hour period is significantly lower than in the first 1000-hour period.

**ADR441 ELECTRICAL CHARACTERISTICS**

$V_{IN} = 3\text{ V to }18\text{ V}$ ,  $T_A = 25^\circ\text{C}$ ,  $C_{IN} = C_{OUT} = 0.1\ \mu\text{F}$ , unless otherwise noted.

**Table 3.**

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
OUTPUT VOLTAGE	$V_O$					
A Grade			2.497	2.500	2.503	V
B Grade			2.499	2.500	2.501	V
INITIAL ACCURACY	$V_{OERR}$					
A Grade					3	mV
B Grade					0.12	%
					1	mV
					0.04	%
TEMPERATURE DRIFT	$TCV_O$					
A Grade		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$		2	10	ppm/ $^\circ\text{C}$
B Grade		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$		1	3	ppm/ $^\circ\text{C}$
LINE REGULATION	$\Delta V_O/\Delta V_{IN}$	$-40^\circ\text{C} < T_A < +125^\circ\text{C}$		10	20	ppm/V
LOAD REGULATION	$\Delta V_O/\Delta I_{LOAD}$	$I_{LOAD} = 0\text{ mA to }10\text{ mA}$ , $V_{IN} = 4\text{ V}$ , $-40^\circ\text{C} < T_A < +125^\circ\text{C}$	-50		+50	ppm/mA
	$\Delta V_O/\Delta I_{LOAD}$	$I_{LOAD} = 0\text{ mA to }-5\text{ mA}$ , $V_{IN} = 4\text{ V}$ , $-40^\circ\text{C} < T_A < +125^\circ\text{C}$	-50		+50	ppm/mA
QUIESCENT CURRENT	$I_{IN}$	No load, $-40^\circ\text{C} < T_A < +125^\circ\text{C}$		3	3.75	mA
VOLTAGE NOISE	$e_N\text{ p-p}$	0.1 Hz to 10 Hz		1.2		$\mu\text{V p-p}$
VOLTAGE NOISE DENSITY	$e_N$	1 kHz		48		nV/ $\sqrt{\text{Hz}}$
TURN-ON SETTLING TIME	$t_R$			10		$\mu\text{s}$
LONG-TERM STABILITY <sup>1</sup>	$V_O$	1000 hours		50		ppm
OUTPUT VOLTAGE HYSTERESIS	$V_{O\_HYS}$			70		ppm
RIPPLE REJECTION RATIO	RRR	$f_{IN} = 1\text{ kHz}$		-80		dB
SHORT CIRCUIT TO GND	$I_{SC}$			27		mA
SUPPLY VOLTAGE OPERATING RANGE	$V_{IN}$		3		18	V
SUPPLY VOLTAGE HEADROOM	$V_{IN} - V_O$		500			mV

<sup>1</sup> The long-term stability specification is noncumulative. The drift in subsequent 1000-hour period is significantly lower than in the first 1000-hour period.

**ADR443 ELECTRICAL CHARACTERISTICS**

$V_{IN} = 3.5 \text{ V to } 18 \text{ V}$ ,  $T_A = 25^\circ\text{C}$ ,  $C_{IN} = C_{OUT} = 0.1 \mu\text{F}$ , unless otherwise noted.

**Table 4.**

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
OUTPUT VOLTAGE	$V_O$					
A Grade			2.996	3.000	3.004	V
B Grade			2.9988	3.000	3.0012	V
INITIAL ACCURACY	$V_{OERR}$					
A Grade					4	mV
					0.13	%
B Grade					1.2	mV
					0.04	%
TEMPERATURE DRIFT	$TCV_O$					
A Grade		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$		2	10	ppm/ $^\circ\text{C}$
B Grade		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$		1	3	ppm/ $^\circ\text{C}$
LINE REGULATION	$\Delta V_O/\Delta V_{IN}$	$-40^\circ\text{C} < T_A < +125^\circ\text{C}$		10	20	ppm/V
LOAD REGULATION	$\Delta V_O/\Delta I_{LOAD}$	$I_{LOAD} = 0 \text{ mA to } 10 \text{ mA}$ , $V_{IN} = 5 \text{ V}$ , $-40^\circ\text{C} < T_A < +125^\circ\text{C}$	-50		+50	ppm/mA
	$\Delta V_O/\Delta I_{LOAD}$	$I_{LOAD} = 0 \text{ mA to } -5 \text{ mA}$ , $V_{IN} = 5 \text{ V}$ , $-40^\circ\text{C} < T_A < +125^\circ\text{C}$	-50		+50	ppm/mA
QUIESCENT CURRENT	$I_{IN}$	No load, $-40^\circ\text{C} < T_A < +125^\circ\text{C}$		3	3.75	mA
VOLTAGE NOISE	$e_N \text{ p-p}$	0.1 Hz to 10 Hz		1.4		$\mu\text{V p-p}$
VOLTAGE NOISE DENSITY	$e_N$	1 kHz		57.6		nV/ $\sqrt{\text{Hz}}$
TURN-ON SETTLING TIME	$t_R$			10		$\mu\text{s}$
LONG-TERM STABILITY <sup>1</sup>	$V_O$	1000 hours		50		ppm
OUTPUT VOLTAGE HYSTERESIS	$V_{O\_HYS}$			70		ppm
RIPPLE REJECTION RATIO	RRR	$f_{IN} = 1 \text{ kHz}$		-80		dB
SHORT CIRCUIT TO GND	$I_{SC}$			27		mA
SUPPLY VOLTAGE OPERATING RANGE	$V_{IN}$		3.5		18	V
SUPPLY VOLTAGE HEADROOM	$V_{IN} - V_O$		500			mV

<sup>1</sup> The long-term stability specification is noncumulative. The drift in the subsequent 1000-hour period is significantly lower than in the first 1000-hour period.

## ADR444 ELECTRICAL CHARACTERISTICS

$V_{IN} = 4.6 \text{ V to } 18 \text{ V}$ ,  $T_A = 25^\circ\text{C}$ ,  $C_{IN} = C_{OUT} = 0.1 \mu\text{F}$ , unless otherwise noted.

Table 5.

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
OUTPUT VOLTAGE	$V_O$					
A Grade			4.091	4.096	4.101	V
B Grade			4.0944	4.096	4.0976	V
INITIAL ACCURACY	$V_{OERR}$					
A Grade					5	mV
					0.13	%
B Grade					1.6	mV
					0.04	%
TEMPERATURE DRIFT	$TCV_O$					
A Grade		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$		2	10	ppm/ $^\circ\text{C}$
B Grade		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$		1	3	ppm/ $^\circ\text{C}$
LINE REGULATION	$\Delta V_O / \Delta V_{IN}$	$-40^\circ\text{C} < T_A < +125^\circ\text{C}$		10	20	ppm/V
LOAD REGULATION	$\Delta V_O / \Delta I_{LOAD}$	$I_{LOAD} = 0 \text{ mA to } 10 \text{ mA}$ , $V_{IN} = 5.5 \text{ V}$ , $-40^\circ\text{C} < T_A < +125^\circ\text{C}$	-50		+50	ppm/mA
	$\Delta V_O / \Delta I_{LOAD}$	$I_{LOAD} = 0 \text{ mA to } -5 \text{ mA}$ , $V_{IN} = 5.5 \text{ V}$ , $-40^\circ\text{C} < T_A < +125^\circ\text{C}$	-50		+50	ppm/mA
QUIESCENT CURRENT	$I_{IN}$	No load, $-40^\circ\text{C} < T_A < +125^\circ\text{C}$		3	3.75	mA
VOLTAGE NOISE	$e_N \text{ p-p}$	0.1 Hz to 10 Hz		1.8		$\mu\text{V p-p}$
VOLTAGE NOISE DENSITY	$e_N$	1 kHz		78.6		nV/ $\sqrt{\text{Hz}}$
TURN-ON SETTLING TIME	$t_R$			10		$\mu\text{s}$
LONG-TERM STABILITY <sup>1</sup>	$V_O$	1000 hours		50		ppm
OUTPUT VOLTAGE HYSTERESIS	$V_{O\_HYS}$			70		ppm
RIPPLE REJECTION RATIO	RRR	$f_{IN} = 1 \text{ kHz}$		-80		dB
SHORT CIRCUIT TO GND	$I_{SC}$			27		mA
SUPPLY VOLTAGE OPERATING RANGE	$V_{IN}$		4.6		18	V
SUPPLY VOLTAGE HEADROOM	$V_{IN} - V_O$		500			mV

<sup>1</sup> The long-term stability specification is noncumulative. The drift in the subsequent 1000-hour period is significantly lower than in the first 1000-hour period.

**ADR445 ELECTRICAL CHARACTERISTICS**

$V_{IN} = 5.5 \text{ V to } 18 \text{ V}$ ,  $T_A = 25^\circ\text{C}$ ,  $C_{IN} = C_{OUT} = 0.1 \mu\text{F}$ , unless otherwise noted.

**Table 6.**

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
OUTPUT VOLTAGE	$V_O$					
A Grade			4.994	5.000	5.006	V
B Grade			4.998	5.000	5.002	V
INITIAL ACCURACY	$V_{OERR}$					
A Grade					6	mV
					0.12	%
B Grade					2	mV
					0.04	%
TEMPERATURE DRIFT	$TCV_O$					
A Grade		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$		2	10	ppm/ $^\circ\text{C}$
B Grade		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$		1	3	ppm/ $^\circ\text{C}$
LINE REGULATION	$\Delta V_O / \Delta V_{IN}$	$-40^\circ\text{C} < T_A < +125^\circ\text{C}$		10	20	ppm/V
LOAD REGULATION	$\Delta V_O / \Delta I_{LOAD}$	$I_{LOAD} = 0 \text{ mA to } 10 \text{ mA}$ , $V_{IN} = 6.5 \text{ V}$ , $-40^\circ\text{C} < T_A < +125^\circ\text{C}$	-50		+50	ppm/mA
	$\Delta V_O / \Delta I_{LOAD}$	$I_{LOAD} = 0 \text{ mA to } -5 \text{ mA}$ , $V_{IN} = 6.5 \text{ V}$ , $-40^\circ\text{C} < T_A < +125^\circ\text{C}$	-50		+50	ppm/mA
QUIESCENT CURRENT	$I_{IN}$	No load, $-40^\circ\text{C} < T_A < +125^\circ\text{C}$		3	3.75	mA
VOLTAGE NOISE	$e_N$ p-p	0.1 Hz to 10 Hz		2.25		$\mu\text{V p-p}$
VOLTAGE NOISE DENSITY	$e_N$	1 kHz		90		nV/ $\sqrt{\text{Hz}}$
TURN-ON SETTLING TIME	$t_R$			10		$\mu\text{s}$
LONG-TERM STABILITY <sup>1</sup>	$V_O$	1000 hours		50		ppm
OUTPUT VOLTAGE HYSTERESIS	$V_{O,HYS}$			70		ppm
RIPPLE REJECTION RATIO	RRR	$f_{IN} = 1 \text{ kHz}$		-80		dB
SHORT CIRCUIT TO GND	$I_{SC}$			27		mA
SUPPLY VOLTAGE OPERATING RANGE	$V_{IN}$		5.5		18	V
SUPPLY VOLTAGE HEADROOM	$V_{IN} - V_O$		500			mV

<sup>1</sup> The long-term stability specification is noncumulative. The drift in the subsequent 1000-hour period is significantly lower than in the first 1000-hour period.

## ABSOLUTE MAXIMUM RATINGS

$T_A = 25^\circ\text{C}$ , unless otherwise noted.

Table 7.

Parameter	Rating
Supply Voltage	20 V
Output Short-Circuit Duration to GND	Indefinite
Storage Temperature Range	$-65^\circ\text{C}$ to $+125^\circ\text{C}$
Operating Temperature Range	$-40^\circ\text{C}$ to $+125^\circ\text{C}$
Junction Temperature Range	$-65^\circ\text{C}$ to $+150^\circ\text{C}$
Lead Temperature, Soldering (60 sec)	$300^\circ\text{C}$

Stresses at or above those listed under Absolute Maximum Ratings may cause permanent damage to the product. This is a stress rating only; functional operation of the product at these or any other conditions above those indicated in the operational section of this specification is not implied. Operation beyond the maximum operating conditions for extended periods may affect product reliability.

## THERMAL RESISTANCE

$\theta_{JA}$  is specified for the worst-case conditions, that is, a device soldered in a circuit board for surface-mount packages.

Table 8. Thermal Resistance

Package Type	$\theta_{JA}$	$\theta_{JC}$	Unit
8-Lead SOIC (R-Suffix)	130	43	$^\circ\text{C}/\text{W}$
8-Lead MSOP (RM-Suffix)	132.5	43.9	$^\circ\text{C}/\text{W}$

## ESD CAUTION



### ESD (electrostatic discharge) sensitive device.

Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

### TYPICAL PERFORMANCE CHARACTERISTICS

$V_{IN} = 7\text{ V}$ ,  $T_A = 25^\circ\text{C}$ ,  $C_{IN} = C_{OUT} = 0.1\ \mu\text{F}$ , unless otherwise noted.

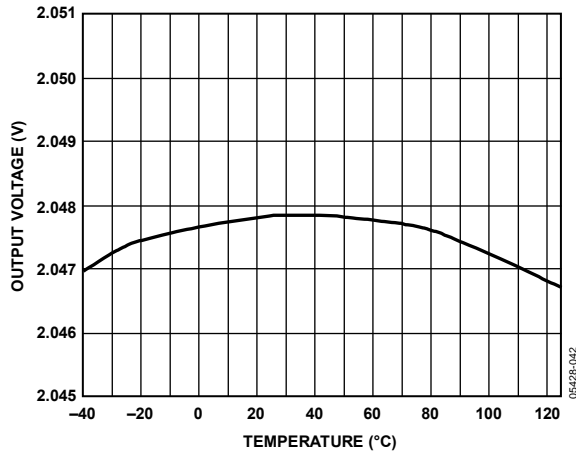


Figure 3. ADR440 Output Voltage vs. Temperature

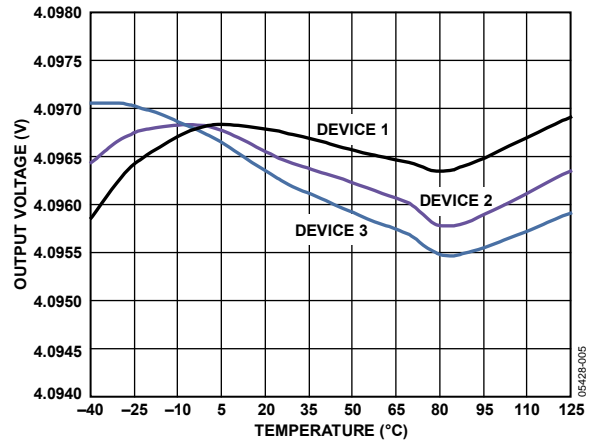


Figure 6. ADR444 Output Voltage vs. Temperature

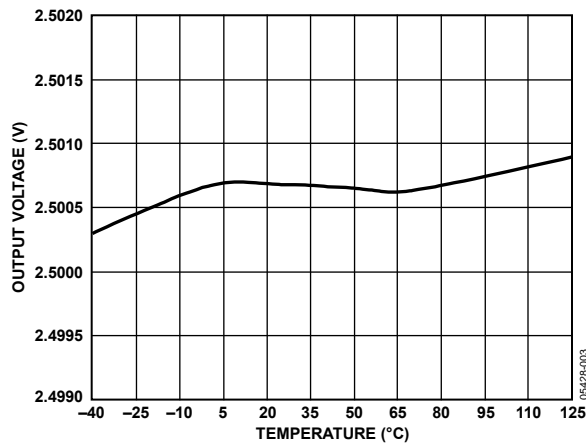


Figure 4. ADR441 Output Voltage vs. Temperature

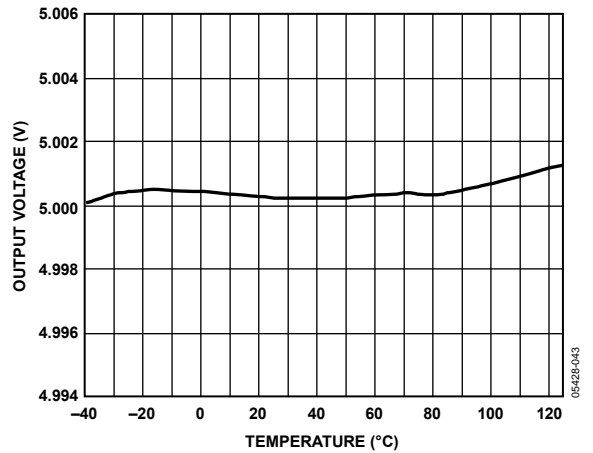


Figure 7. ADR445 Output Voltage vs. Temperature

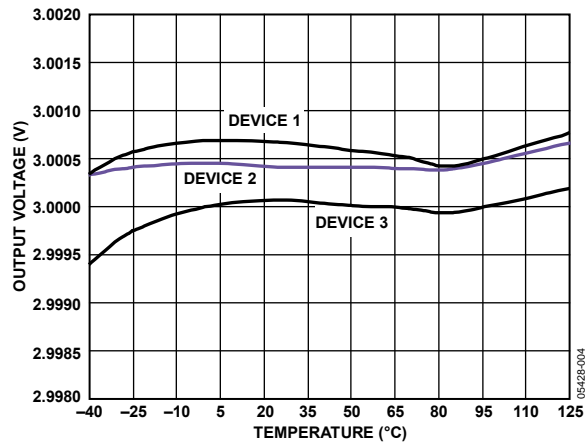


Figure 5. ADR443 Output Voltage vs. Temperature

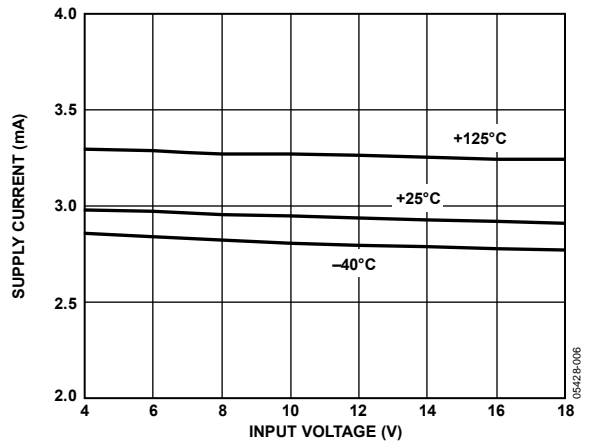


Figure 8. ADR441 Supply Current vs. Input Voltage



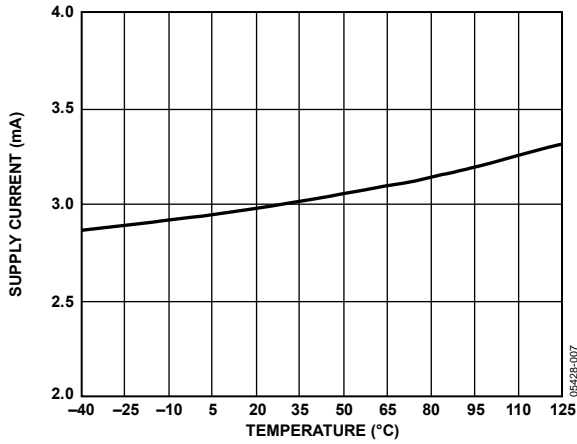


Figure 9. ADR441 Supply Current vs. Temperature

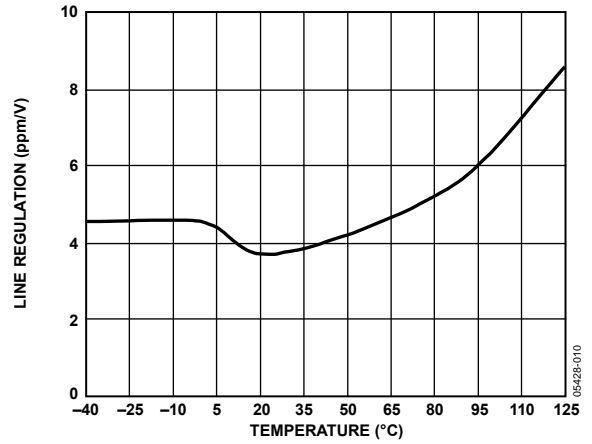


Figure 12. ADR441 Line Regulation vs. Temperature

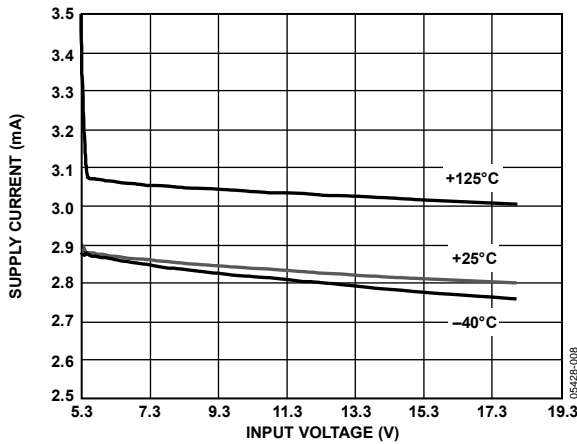


Figure 10. ADR445 Supply Current vs. Input Voltage

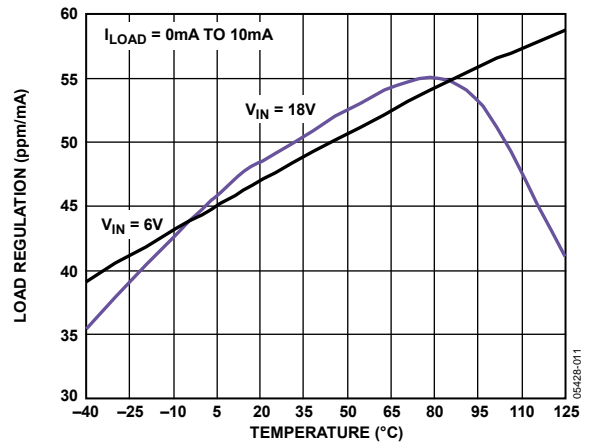


Figure 13. ADR441 Load Regulation vs. Temperature

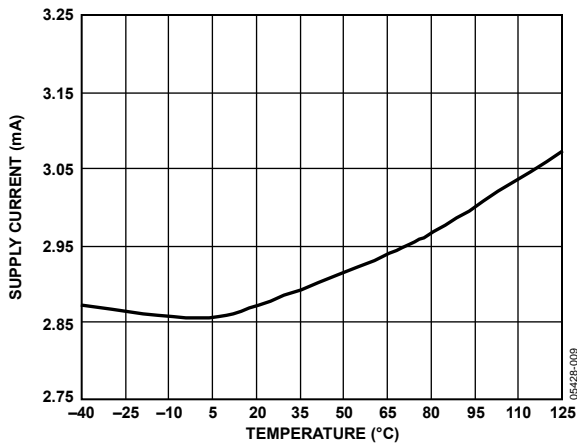


Figure 11. ADR445 Supply Current vs. Temperature

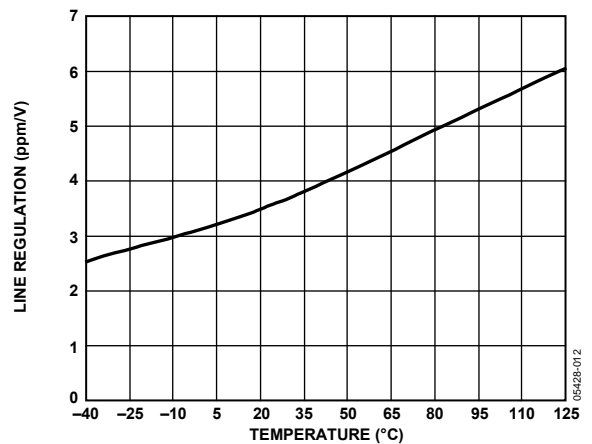


Figure 14. ADR445 Line Regulation vs. Temperature

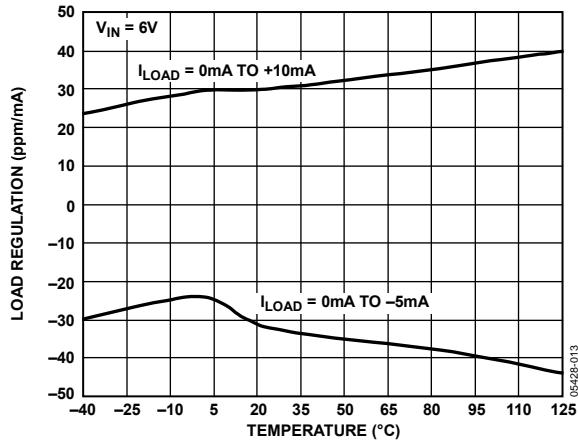


Figure 15. ADR445 Load Regulation vs. Temperature

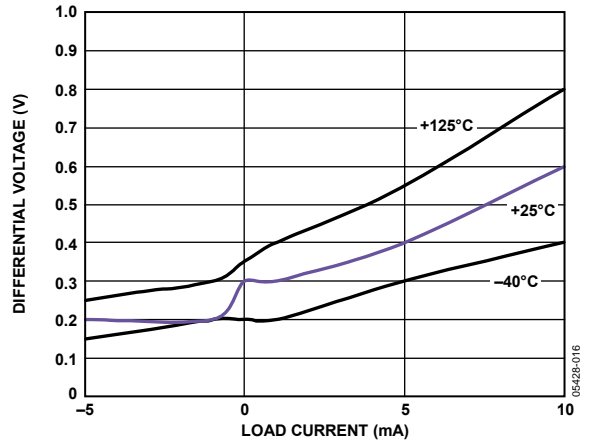


Figure 18. ADR445 Minimum Input/Output Differential Voltage vs. Load Current

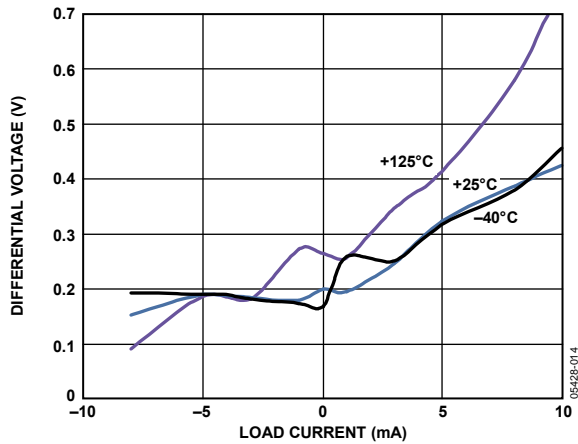


Figure 16. ADR441 Minimum Input/Output Differential Voltage vs. Load Current

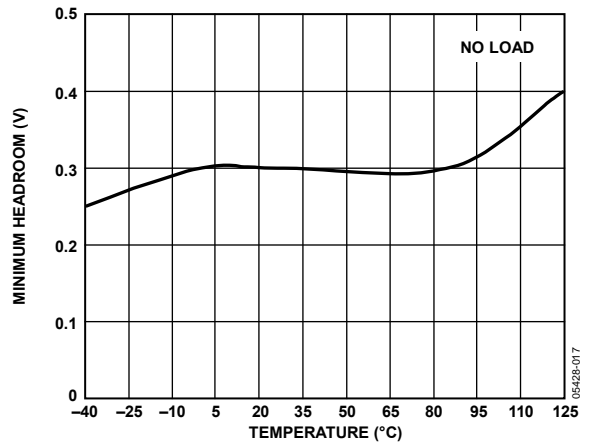


Figure 19. ADR445 Minimum Headroom vs. Temperature

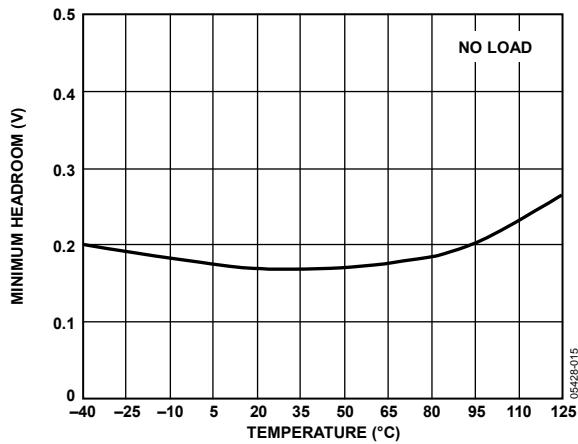


Figure 17. ADR441 Minimum Headroom vs. Temperature

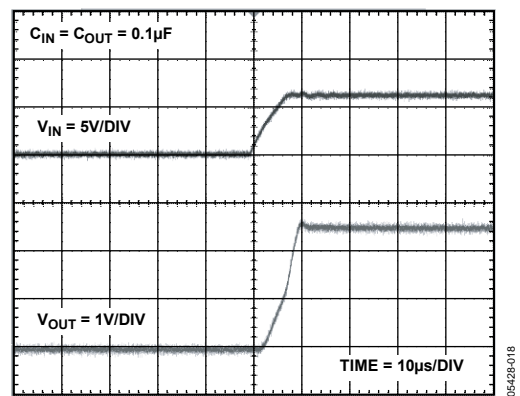


Figure 20. ADR441 Turn-On Response

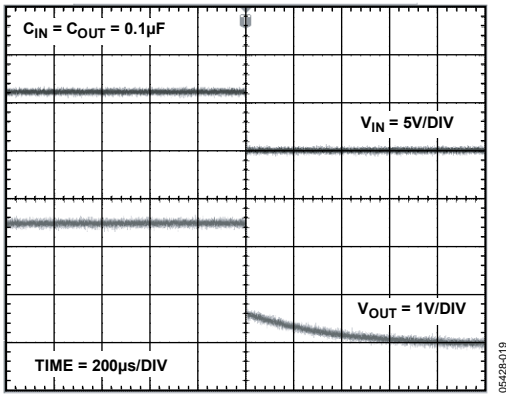


Figure 21. ADR441 Turn-Off Response

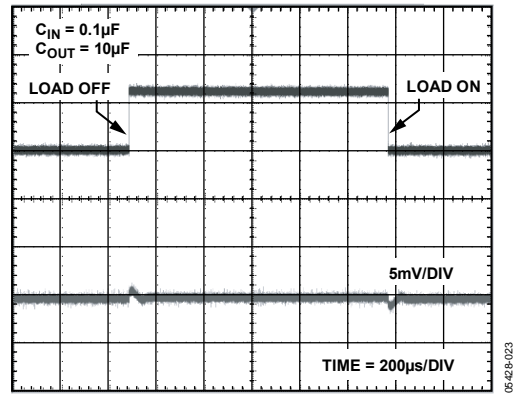


Figure 24. ADR441 Load Transient Response

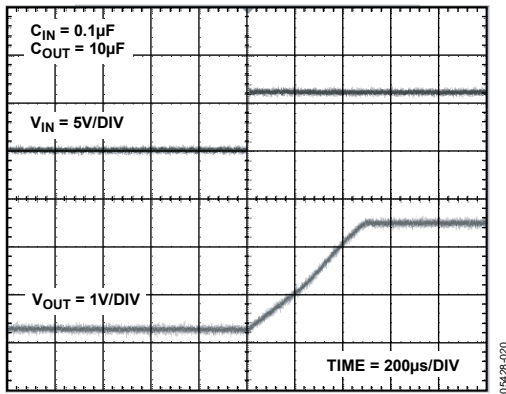


Figure 22. ADR441 Turn-On Response

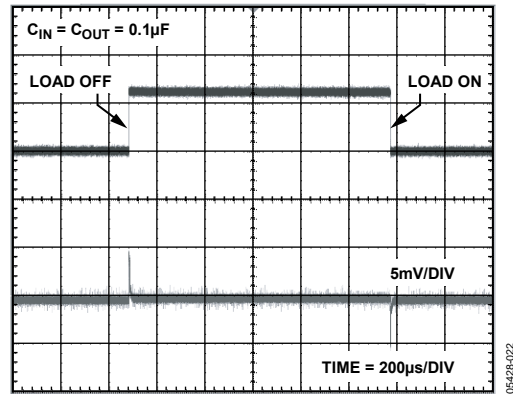


Figure 25. ADR441 Load Transient Response

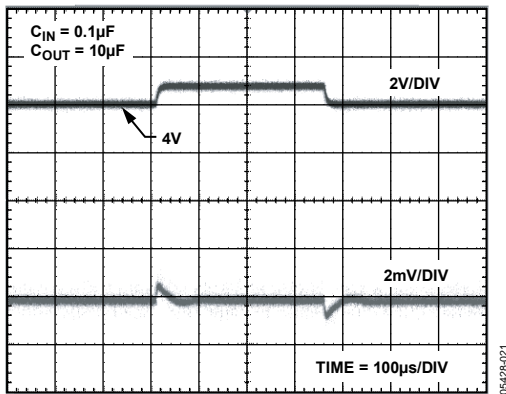


Figure 23. ADR441 Line Transient Response

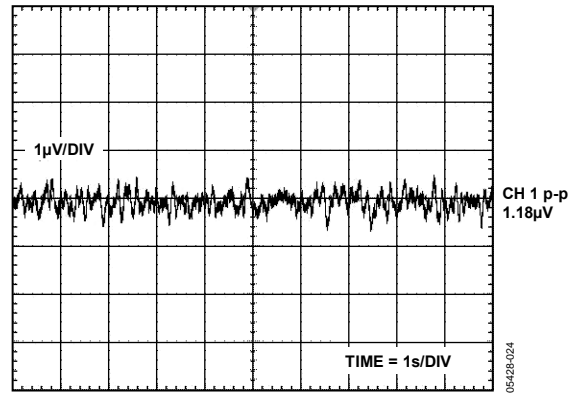


Figure 26. ADR441 0.1 Hz to 10.0 Hz Voltage Noise

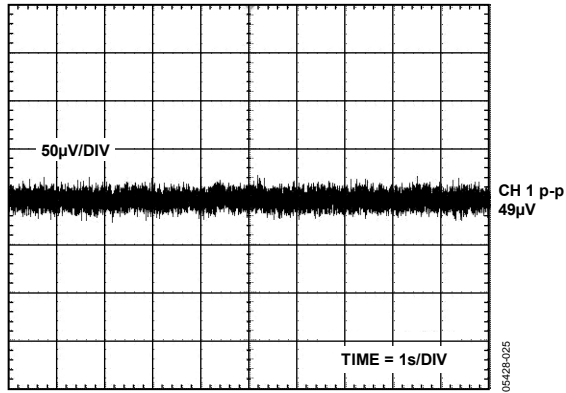


Figure 27. ADR441 10 Hz to 10 kHz Voltage Noise

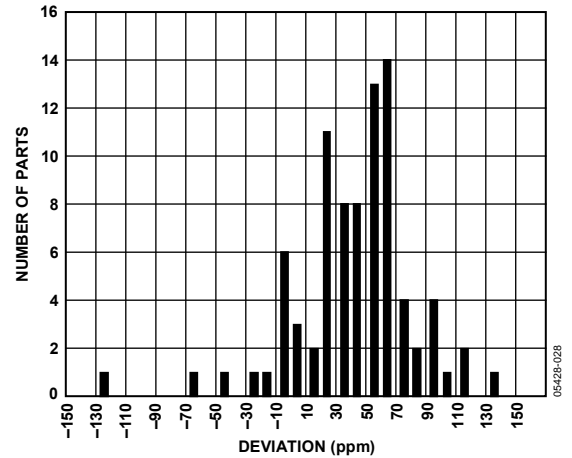


Figure 30. ADR441 Typical Output Voltage Hysteresis

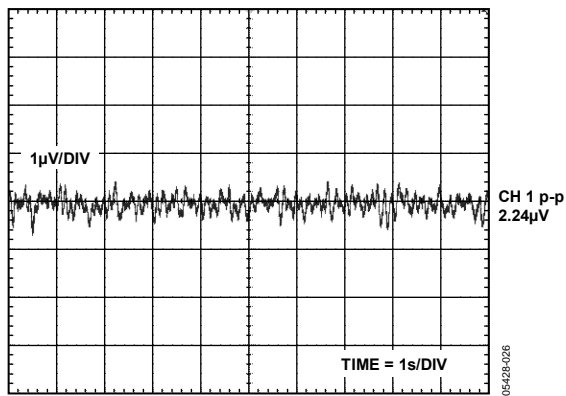


Figure 28. ADR445 0.1 Hz to 10.0 Hz Voltage Noise

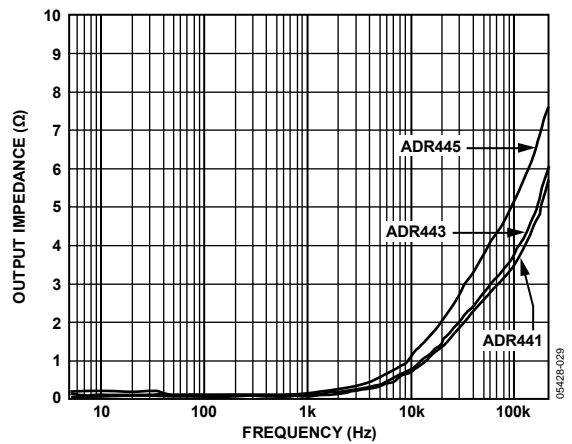


Figure 31. Output Impedance vs. Frequency

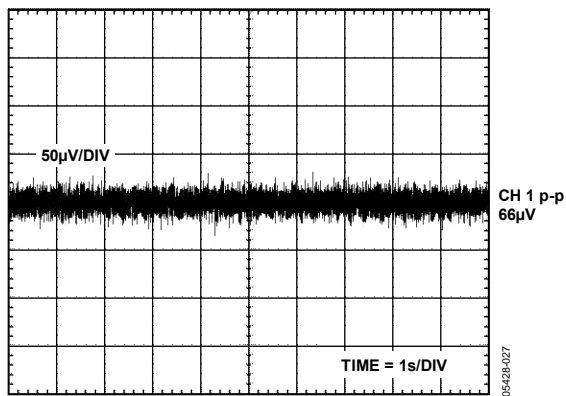


Figure 29. ADR445 10 Hz to 10 kHz Voltage Noise

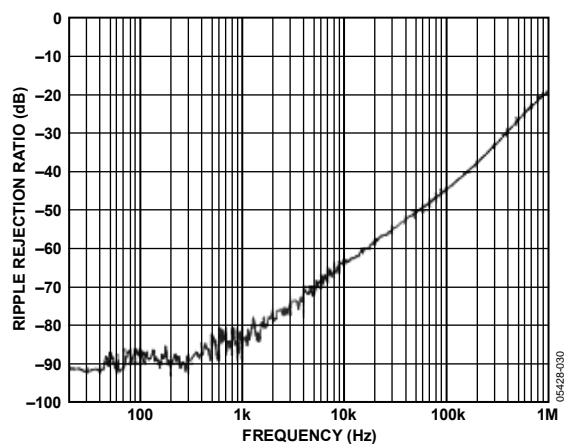


Figure 32. Ripple Rejection Ratio vs. Frequency

## THEORY OF OPERATION

The ADR44x series of references uses a new reference generation technique known as XFET (eXtra implanted junction FET). This technique yields a reference with low dropout, good thermal hysteresis, and exceptionally low noise. The core of the XFET reference consists of two junction field-effect transistors (JFETs), one of which has an extra channel implant to raise its pinch-off voltage. By running the two JFETs at the same drain current, the difference in pinch-off voltage can be amplified and used to form a highly stable voltage reference.

The intrinsic reference voltage is around 0.5 V with a negative temperature coefficient of about -120 ppm/°C. This slope is essentially constant to the dielectric constant of silicon, and it can be closely compensated for by adding a correction term generated in the same fashion as the proportional-to-absolute temperature (PTAT) term used to compensate band gap references. The advantage of an XFET reference is its correction term, which is approximately 20 times lower and requires less correction than that of a band gap reference. Because most of the noise of a band gap reference comes from the temperature compensation circuitry, the XFET results in much lower noise.

Figure 33 shows the basic topology of the ADR44x series. The temperature correction term is provided by a current source with a value designed to be proportional to the absolute temperature. The general equation is

$$V_{OUT} = G (\Delta V_P - R1 \times I_{PTAT}) \tag{1}$$

where:

G is the gain of the reciprocal of the divider ratio.  
 $\Delta V_P$  is the difference in pinch-off voltage between the two JFETs.  
 $I_{PTAT}$  is the positive temperature coefficient correction current.

ADR44x devices are created by on-chip adjustment of R2 and R3 to achieve the different voltage options at the reference output.

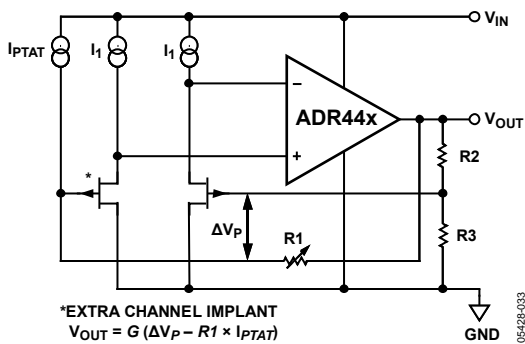


Figure 33. Simplified Schematic Device

## POWER DISSIPATION CONSIDERATIONS

The ADR44x family of references is guaranteed to deliver load currents to 10 mA with an input voltage that ranges from 3 V to 18 V. When these devices are used in applications at higher currents, use the following equation to account for the temperature effects of increases in power dissipation:

$$T_J = P_D \times \theta_{JA} + T_A \tag{2}$$

where:

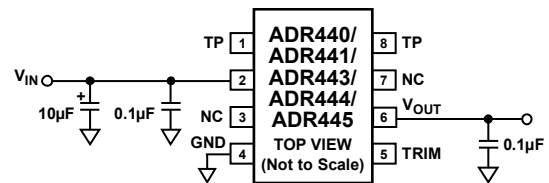
$T_J$  and  $T_A$  are the junction and ambient temperatures, respectively.

$P_D$  is the device power dissipation.

$\theta_{JA}$  is the device package thermal resistance.

## BASIC VOLTAGE REFERENCE CONNECTIONS

The ADR44x family requires a 0.1 μF capacitor on the input and the output for stability. Although not required for operation, a 10 μF capacitor at the input can help with line voltage transient performance.



- NOTES  
 1. NC = NO CONNECT  
 2. TP = TEST PIN (DO NOT CONNECT)

Figure 34. Basic Voltage Reference Configuration

## NOISE PERFORMANCE

The noise generated by the ADR44x family of references is typically less than 1.4 μV p-p over the 0.1 Hz to 10.0 Hz band for ADR440, ADR441, and ADR443. Figure 26 shows the 0.1 Hz to 10 Hz noise of the ADR441, which is only 1.2 μV p-p. The noise measurement is made with a band-pass filter composed of a 2-pole high-pass filter with a corner frequency at 0.1 Hz and a 2-pole low-pass filter with a corner frequency at 10.0 Hz.

## TURN-ON TIME

Upon application of power (cold start), the time required for the output voltage to reach its final value within a specified error band is defined as the turn-on settling time. Two components normally associated with this are the time for the active circuits to settle and the time for the thermal gradients on the chip to stabilize. Figure 20 and Figure 21 show the turn-on and turn-off settling times for the ADR441.

## APPLICATIONS INFORMATION

### OUTPUT ADJUSTMENT

The ADR44x family features a TRIM pin that allows the user to adjust the output voltage of the part over a limited range. This allows errors from the reference and overall system errors to be trimmed out by connecting a potentiometer between the output and the ground, with the wiper connected to the TRIM pin. Figure 35 shows the optimal trim configuration. R1 allows fine adjustment of the output and is not always required. R<sub>P</sub> should be sufficiently large so that the maximum output current from the ADR44x is not exceeded.

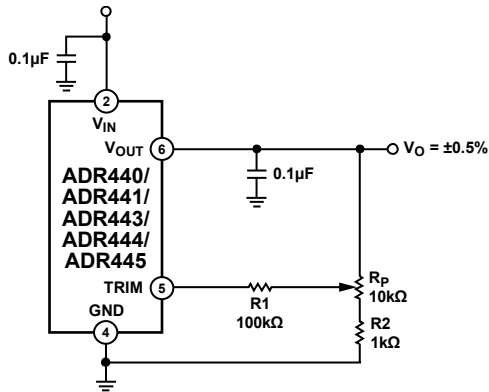


Figure 35. ADR44x Trim Function

Using the trim function has a negligible effect on the temperature performance of the ADR44x. However, all resistors need to be low temperature coefficient resistors, or errors may occur.

### BIPOLAR OUTPUTS

By connecting the output of the ADR44x to the inverting terminal of an operational amplifier, it is possible to obtain both positive and negative reference voltages. Care must be taken when choosing Resistors R1 and R2 (see Figure 36). These resistors must be matched as closely as possible to ensure minimal differences between the negative and positive outputs. In addition, care must be taken to ensure performance over temperature. Use low temperature coefficient resistors if the circuit is used over temperature; otherwise, differences exist between the two outputs.

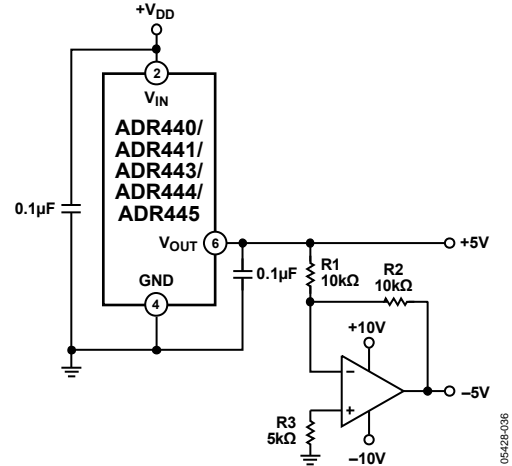


Figure 36. ADR44x Bipolar Outputs

### PROGRAMMABLE VOLTAGE SOURCE

To obtain different voltages than those offered by the ADR44x, some extra components are needed. In Figure 37, two potentiometers are used to set the desired voltage and the buffering amplifier provides current drive. The potentiometer connected between V<sub>OUT</sub> and GND, with its wiper connected to the noninverting input of the operational amplifier, takes care of coarse trim. The second potentiometer, with its wiper connected to the trim terminal of the ADR44x, is used for fine adjustment. Resolution depends on the end-to-end resistance value and the resolution of the selected potentiometer.

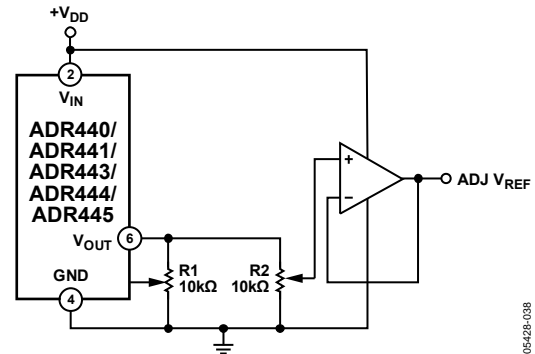


Figure 37. Programmable Voltage Source

For a completely programmable solution, replace the two potentiometers in Figure 37 with one Analog Devices dual digital potentiometer, offered with either an SPI or an I<sup>2</sup>C interface. These interfaces set the position of the wiper on both potentiometers and allow the output voltage to be set. Table 9 lists compatible Analog Devices digital potentiometers.

Table 9. Digital Potentiometer Parts

Part No.	No. of Channels	No. of Positions	ITF	R (kΩ)	V <sub>DD</sub> <sup>1</sup> (V)
AD5251	2.00	64.00	I <sup>2</sup> C	1, 10, 50, 100	5.5
AD5207	2.00	256.00	SPI	10, 50, 100	5.5
AD5242	2.00	256.00	I <sup>2</sup> C	10, 100, 1M	5.5
AD5262	2.00	256.00	SPI	20, 50, 200	15
AD5282	2.00	256.00	I <sup>2</sup> C	20, 50, 100	15
AD5252	2.00	256.00	I <sup>2</sup> C	1, 10, 50, 100	5.5
AD5232	2.00	256.00	SPI	10, 50, 100	5.5
AD5235	2.00	1024.00	SPI	25, 250	5.5
ADN2850	2.00	1024.00	SPI	25, 250	5.5

<sup>1</sup> Can also use a negative supply.

Adding a negative supply to the operational amplifier allows the user to produce a negative programmable reference by connecting the reference output to the inverting terminal of the operational amplifier. Choose feedback resistors to minimize errors over temperature.

**PROGRAMMABLE CURRENT SOURCE**

It is possible to build a programmable current source using a setup similar to the programmable voltage source, as shown in Figure 38. The constant voltage on the gate of the transistor sets the current through the load. Varying the voltage on the gate changes the current. This circuit does not require a dual digital potentiometer.

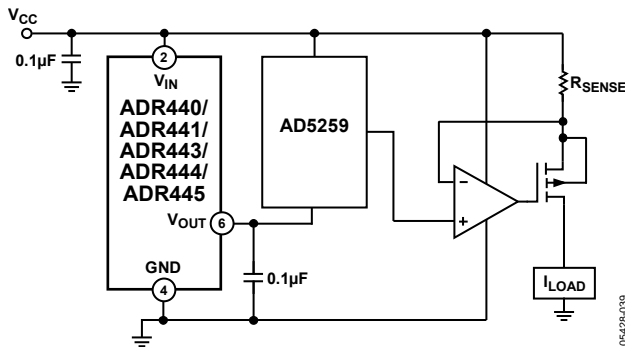


Figure 38. Programmable Current Source

**HIGH VOLTAGE FLOATING CURRENT SOURCE**

Use the circuit in Figure 39 to generate a floating current source with minimal self heating. This particular configuration can operate on high supply voltages, determined by the breakdown voltage of the N-channel JFET.

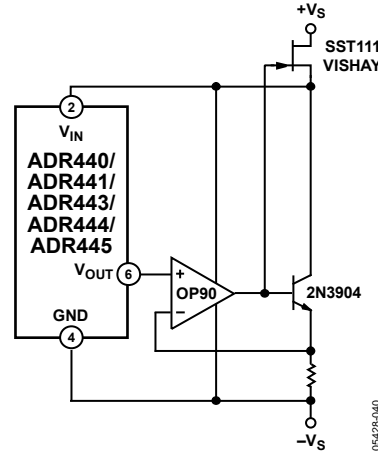


Figure 39. Floating Current Source

**PRECISION OUTPUT REGULATOR (BOOSTED REFERENCE)**

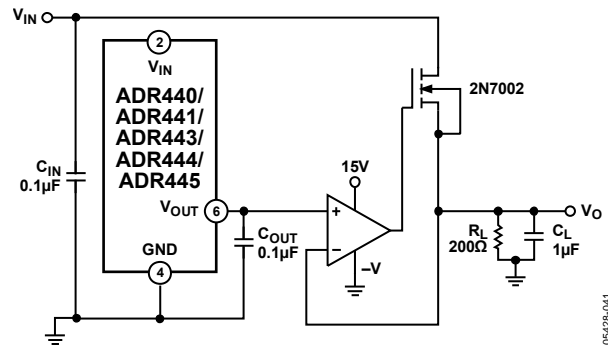
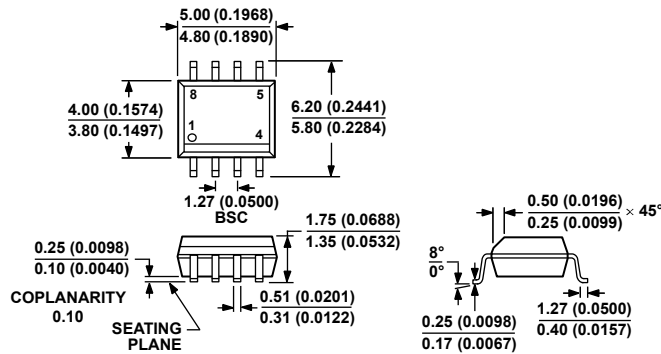


Figure 40. Boosted Output Reference

Higher current drive capability can be obtained without sacrificing accuracy by using the circuit in Figure 40. The operational amplifier regulates the MOSFET turn-on, forcing V<sub>O</sub> to equal the V<sub>REF</sub>. Current is then drawn from V<sub>IN</sub>, allowing increased current drive capability. The circuit allows a 50 mA load; if higher current drive is required, use a larger MOSFET. For fast transient response, add a buffer at V<sub>O</sub> to aid with capacitive loading.

OUTLINE DIMENSIONS

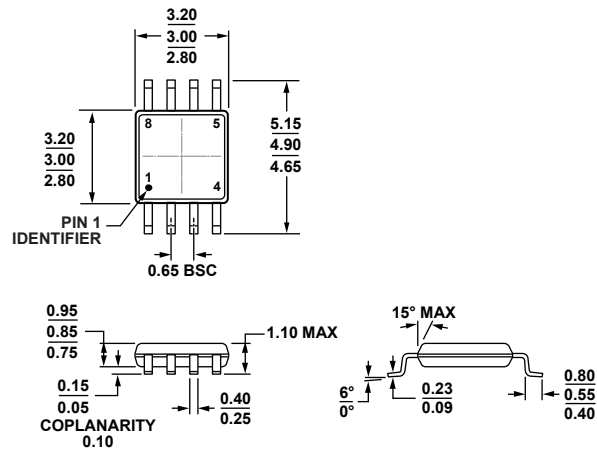


COMPLIANT TO JEDEC STANDARDS MS-012-AA  
 CONTROLLING DIMENSIONS ARE IN MILLIMETERS; INCH DIMENSIONS  
 (IN PARENTHESES) ARE ROUNDED-OFF MILLIMETER EQUIVALENTS FOR  
 REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN.

Figure 41. 8-Lead Standard Small Outline Package [SOIC\_N]  
 Narrow Body  
 (R-8)

Dimensions shown in millimeters and (inches)

012407-A



COMPLIANT TO JEDEC STANDARDS MO-187-AA

Figure 42. 8-Lead Mini Small Outline Package [MSOP]  
 (RM-8)

Dimensions show in millimeters

10-07-2008-B



## ORDERING GUIDE

Model <sup>1</sup>	Output Voltage (V)	Initial Accuracy		Temperature Coefficient Package (ppm/°C)	Package Description	Branding	Temperature Range	Package Option
		±mV	%					
ADR440ARZ	2.048	3	0.15	10	8-Lead SOIC_N		-40°C to +125°C	R-8
ADR440ARZ-REEL7	2.048	3	0.15	10	8-Lead SOIC_N		-40°C to +125°C	R-8
ADR440ARMZ	2.048	3	0.15	10	8-Lead MSOP	R01	-40°C to +125°C	RM-8
ADR440ARMZ-REEL7	2.048	3	0.15	10	8-Lead MSOP	R01	-40°C to +125°C	RM-8
ADR440BRZ	2.048	1	0.05	3	8-Lead SOIC_N		-40°C to +125°C	R-8
ADR440BRZ-REEL7	2.048	1	0.05	3	8-Lead SOIC_N		-40°C to +125°C	R-8
ADR441ARZ	2.500	3	0.12	10	8-Lead SOIC_N		-40°C to +125°C	R-8
ADR441ARZ-REEL7	2.500	3	0.12	10	8-Lead SOIC_N		-40°C to +125°C	R-8
ADR441ARMZ	2.500	3	0.12	10	8-Lead MSOP	R02	-40°C to +125°C	RM-8
ADR441ARMZ-REEL7	2.500	3	0.12	10	8-Lead MSOP	R02	-40°C to +125°C	RM-8
ADR441BRZ	2.500	1	0.04	3	8-Lead SOIC_N		-40°C to +125°C	R-8
ADR441BRZ-REEL7	2.500	1	0.04	3	8-Lead SOIC_N		-40°C to +125°C	R-8
ADR443ARZ	3.000	4	0.13	10	8-Lead SOIC_N		-40°C to +125°C	R-8
ADR443ARZ-REEL7	3.000	4	0.13	10	8-Lead SOIC_N		-40°C to +125°C	R-8
ADR443ARMZ	3.000	4	0.13	10	8-Lead MSOP	R03	-40°C to +125°C	RM-8
ADR443ARMZ-REEL7	3.000	4	0.13	10	8-Lead MSOP	R03	-40°C to +125°C	RM-8
ADR443BRZ	3.000	1.2	0.04	3	8-Lead SOIC_N		-40°C to +125°C	R-8
ADR443BRZ-REEL7	3.000	1.2	0.04	3	8-Lead SOIC_N		-40°C to +125°C	R-8
ADR444ARZ	4.096	5	0.13	10	8-Lead SOIC_N		-40°C to +125°C	R-8
ADR444ARZ-REEL7	4.096	5	0.13	10	8-Lead SOIC_N		-40°C to +125°C	R-8
ADR444ARMZ	4.096	5	0.13	10	8-Lead MSOP	R04	-40°C to +125°C	RM-8
ADR444ARMZ-REEL7	4.096	5	0.13	10	8-Lead MSOP	R04	-40°C to +125°C	RM-8
ADR444BRZ	4.096	1.6	0.04	3	8-Lead SOIC_N		-40°C to +125°C	R-8
ADR444BRZ-REEL7	4.096	1.6	0.04	3	8-Lead SOIC_N		-40°C to +125°C	R-8
ADR445ARZ	5.000	6	0.12	10	8-Lead SOIC_N		-40°C to +125°C	R-8
ADR445ARZ-REEL7	5.000	6	0.12	10	8-Lead SOIC_N		-40°C to +125°C	R-8
ADR445ARMZ	5.000	6	0.12	10	8-Lead MSOP	R05	-40°C to +125°C	RM-8
ADR445ARMZ-REEL7	5.000	6	0.12	10	8-Lead MSOP	R05	-40°C to +125°C	RM-8
ADR445BRZ	5.000	2	0.04	3	8-Lead SOIC_N		-40°C to +125°C	R-8
ADR445BRZ-REEL7	5.000	2	0.04	3	8-Lead SOIC_N		-40°C to +125°C	R-8

<sup>1</sup> Z = RoHS Compliant Part.

<sup>2</sup>C refers to a communications protocol originally developed by Philips Semiconductors (now NXP Semiconductors).